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Small Signal MOSFET

60 V, 115 mA, N-Channel SOT-23

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Drain Current - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1) - Pulsed (Note 2)	I _D I _D I _{DM}	±115 ±75 ±800	mAdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \le 50 \mu s$)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 3) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(Note 4) T _A = 25°C	P _D	300	mW mW/°C
Derate above 25°C	VI.T.	2.4	WWI
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
- 3. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 4. Alumina = $0.4 \times 0.3 \times 0.025$ in 99.5% alumina.



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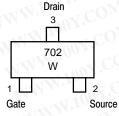
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
60 V	7.5 Ω @ 10 V, 500 mA	115 mA

N-Channel 3 1 0 2

MARKING DIAGRAM & PIN ASSIGNMENT



SOT-23 CASE 318 STYLE 21



702 = Device Code W = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]				
2N7002LT1	SOT-23	3000 Tape & Reel				
2N7002LT3	001 20	10,000 Tape & Reel				
2N7002LT1G	SOT-23	3000 Tape & Reel				
2N7002LT3G	(Pb-free)	10,000 Tape & Reel				

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Ch	aracteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	W.1001.COM.TW	I.WW.	00 - 100	Mil		
Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)		V _{(BR)DSS}	60	OM.TW	-	Vdc
Zero Gate Voltage Drain Curren (V _{GS} = 0, V _{DS} = 60 Vdc)	t $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _{DSS}	V.1001.	0M.T.	1.0 500	μAdc
Gate-Body Leakage Current, Fo (V _{GS} = 20 Vdc)	orward COM TO	I _{GSSF}	1.100X	V.COM.T	100	nAdc
Gate-Body Leakage Current, Ro (V _{GS} = -20 Vdc)	everse	I _{GSSR}	MAT 100	N.COM	-100	nAdc
ON CHARACTERISTICS (Note	5) WYW COM	1	NWW	WAY.CO.	TIN	
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250 \mu Adc$)	WWW.100Y.COM.T	V _{GS(th)}	1.0	1001-CO	2.5	Vdc
On-State Drain Current $(V_{DS} \ge 2.0 V_{DS(on)}, V_{GS} = 10$	Vdc)	I _{D(on)}	500	1007.	OMATY	mA
Static Drain–Source On–State V $(V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAd})$ $(V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAd})$	V _{DS(on)}	-WA	N.1007.	3.75 0.375	Vdc	
$ \begin{array}{llllllllllllllllllllllllllllllllllll$		r _{DS(on)}	- W	N.M. = 100 N.M. = 100	7.5 13.5 7.5 13.5	Ohms
Forward Transconductance $(V_{DS} \ge 2.0 V_{DS(on)}, I_D = 200 \text{ mA}$	TAN MAN 100XY	9FS	80	WWW.	100 - 100 - 100 -	mmhos
DYNAMIC CHARACTERISTICS		COM	NY - XX	THE WAY	1.100	COM
Input Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f =	W.14 W. 100.	C _{iss}	TW	MM	50	pF
Output Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 3	1.0 MHz)	C _{oss}	1.T*	-WV	25	pF
Reverse Transfer Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f =	1.0 MHz)	C _{rss}	M.T.	- 7	5.0	pF
SWITCHING CHARACTERISTI	CS (Note 5)	I.T. C	OM	N .	MMM.	any.C'
Turn-On Delay Time	$(V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc},$	t _{d(on)}	$CO_{\overline{M}_{1}, r}$		20	ns
Turn-Off Delay Time	$R_G = 25 \Omega$, $R_L = 50 \Omega$, $V_{gen} = 10 V$)	t _{d(off)}	COMI	_	40	ns
BODY-DRAIN DIODE RATING	\$ 00 J. W.I.	100°	MOM.	IN	TXXI'	W.100
Diode Forward On-Voltage (I _S = 11.5 mAdc, V _{GS} = 0 V)	V.100Y.COM.TW	V _{SD}	N.COM	TW_	-1.5	Vdc
Source Current Continuous (Body Diode)		Is	001.CO	M.TW	-115	mAdc
Source Current Pulsed	M. T.	I _{SM}	100₹.C¢	WEIN	-800	mAdc
5. Pulse Test: Pulse Width ≤ 300	μs, Duty Cycle ≤ 2.0%.	MMA	N.100Y.C	COM.TW	N ·	MMA

WWW.100Y.COM.TW 5. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

WWW.100Y.COM.TW TYPICAL ELECTRICAL CHARACTERISTICS

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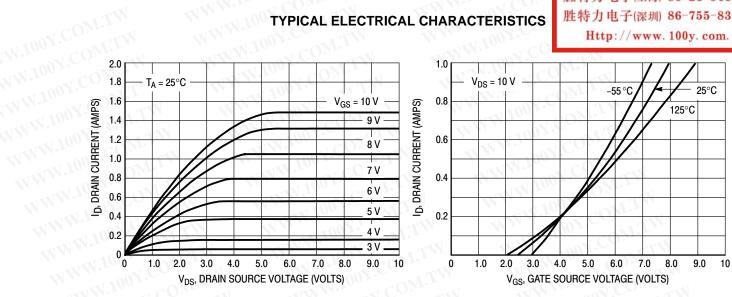


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

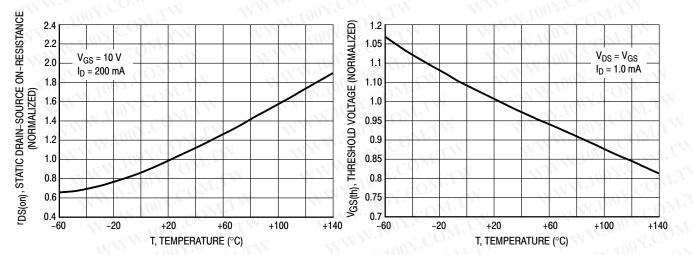


Figure 3. Temperature versus Static **Drain-Source On-Resistance**

Figure 4. Temperature versus Gate **Threshold Voltage**

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WW.100Y.COM.TW .100Y.COM.TW **PACKAGE DIMENSIONS**

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SOT-23 (TO-236) CASE 318-08 **ISSUE AH**

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NOTES:

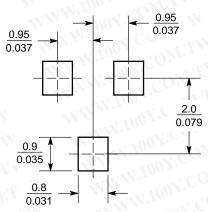
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- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS
 IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 318-03 AND -07 OBSOLETE, NEW STANDARD

	INCHES	CHES	MILLIN	METERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.1102	0.1197	2.80	3.04		
В	0.0472	0.0551	1.20	1.40		
С	0.0350	0.0440	0.89	1.11		
D	0.0150	0.0200	0.37	0.50		
G	0.0701	0.0807	1.78	2.04		
Н	0.0005	0.0040	0.013	0.100		
J	0.0034	0.0070	0.085	0.177		
K	0.0140	0.0285	0.35	0.69		
L	0.0350	0.0401	0.89	1.02		
S	0.0830	0.1039	2.10	2.64		
٧	0.0177	0.0236	0.45	0.60		

STYLE 21:

- PIN 1. GATE 2. SOUR
 - SOURCE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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